MOSFETs Silicon P-Channel MOS (U-MOSVI)

# TJ80S04M3L

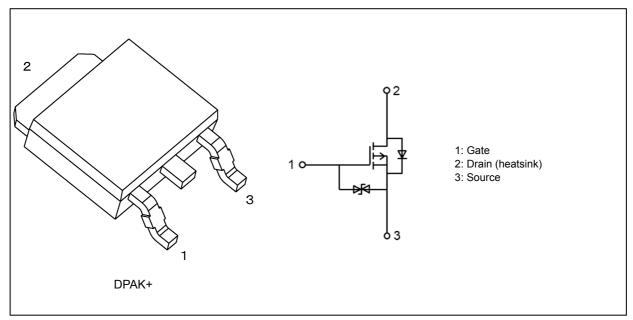
#### 1. Applications

- Automotive
- Motor Drivers
- DC-DC Converters
- Switching Voltage Regulators

### 2. Features

- (1) AEC-Q101 qualified
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 4.0 \text{ m}\Omega$  (typ.) ( $V_{GS} = -10 \text{ V}$ )
- (3) Low leakage current:  $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -40 \ V)$
- (4) Enhancement mode:  $V_{th}$  = -2.0 to -3.0 V ( $V_{DS}$  = -10 V,  $I_D$  = -1 mA)

#### 3. Packaging and Internal Circuit



Rev.10.0

#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics				Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	-40	V
Gate-source voltage			V <sub>GSS</sub>	-20/+10	1
Drain current (DC)		(Note 1)	Ι <sub>D</sub>	-80	Α
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	-160	
Power dissipation	(T <sub>c</sub> = 25°C)		PD	100	W
Single-pulse avalanche energy		(Note 2)	E <sub>AS</sub>	148	mJ
Avalanche current			I <sub>AR</sub>	-80	Α
Channel temperature		(Note 3)	T <sub>ch</sub>	175	°C
Storage temperature		(Note 3)	T <sub>stg</sub>	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	1.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 175°C.

Note 2: V\_DD = -25 V, T\_ch = 25°C (initial), L = 24  $\mu H,\,R_G$  = 25  $\Omega,\,I_{AR}$  = -80 A

Note 3: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics

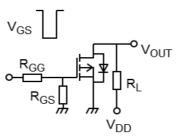
## 6.1. Static Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = -16/+10 V, V <sub>DS</sub> = 0 V	_	_	±10	μA
Drain cut-off current	I <sub>DSS</sub>	$V_{DS}$ = -40 V, $V_{GS}$ = 0 V	_	_	-10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V	-40	—	_	V
Drain-source breakdown voltage (Note 4)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 10 V	-30	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-2.0	_	-3.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -6 V, I <sub>D</sub> = -40 A		5.1	7.9	mΩ
		V <sub>GS</sub> = -10 V, I <sub>D</sub> = -40 A	_	4.0	5.2	

Note 4: If a forward bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	7770	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	740	—	
Output capacitance	C <sub>oss</sub>		_	970	_	
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	_	100	—	ns
Switching time (turn-on time)	t <sub>on</sub>		_	125	—	
Switching time (fall time)	t <sub>f</sub>		_	300	—	
Switching time (turn-off time)	t <sub>off</sub>		_	970		



$$\begin{split} V_{DD} &\approx -20 \ V \\ V_{GS} &= 0 \ V/-10 \ V \\ I_D &= -40 \ A \\ R_L &= 0.5 \ \Omega \\ R_{GG} &= R_{GS} &= 4.7 \ \Omega \\ Duty &\leq 1 \ \%, \ t_w &= 10 \ \mu s \end{split}$$

#### Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD}\approx$ -32 V, $V_{GS}$ = -10 V, $I_{D}$ = -80 A	_	158	—	nC
Gate-source charge	Q <sub>gs</sub>		_	106	_	
Gate-drain charge	Q <sub>gd</sub>		_	52	_	

### 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 5)	I <sub>DR</sub>	—	_	_	-80	A
Reverse drain current (pulsed)	(Note 5)	I <sub>DRP</sub>	—	_		-160	
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = -80 A, V <sub>GS</sub> = 0 V	_		1.2	V
Reverse recovery time		t <sub>rr</sub>	I <sub>DR</sub> = -80 A, V <sub>GS</sub> = 0 V	_	50	_	ns
Reverse recovery charge		Q <sub>rr</sub>	dl <sub>DR</sub> /dt = 50 A/µs	_	33	_	nC

Note 5: Ensure that the channel temperature does not exceed 175°C.

### 7. Marking (Note)

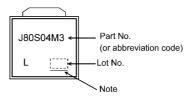
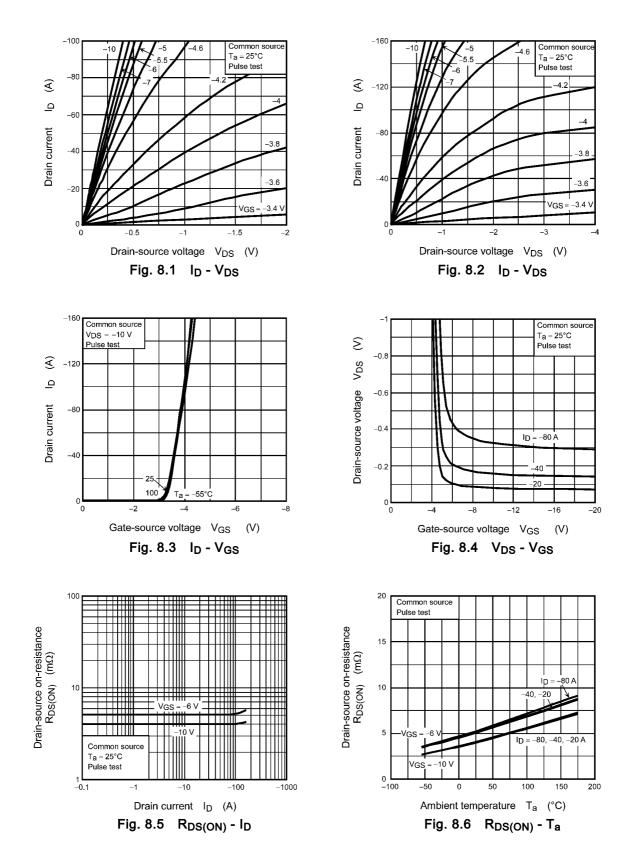
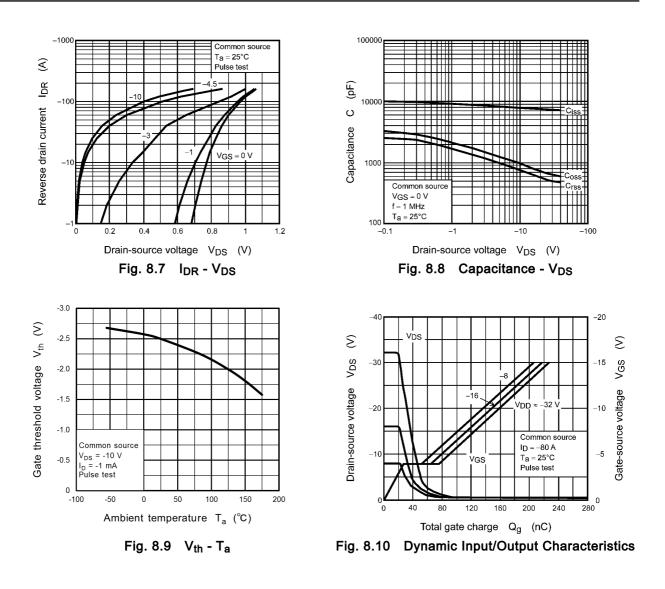


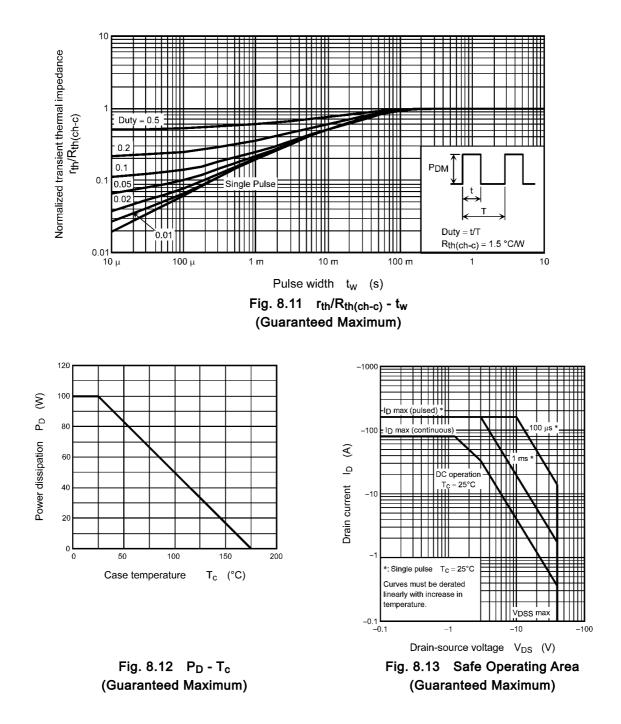
Fig. 7.1 Marking

 Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]
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#### 8. Characteristics Curves (Note)



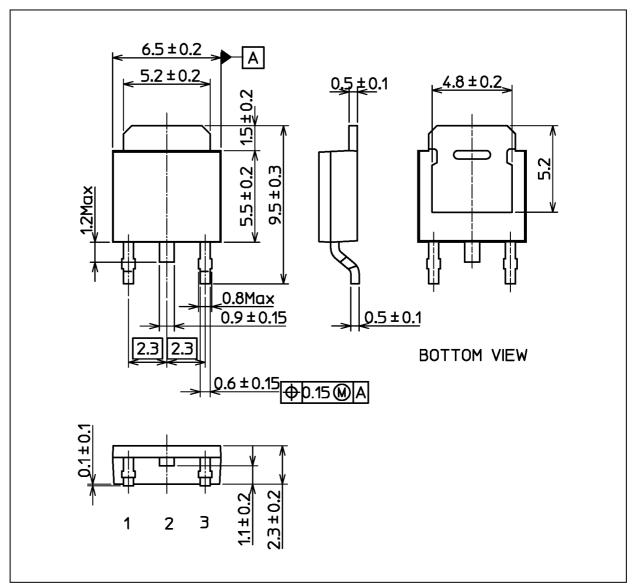




Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

	Package Name(s)
TOSHIBA: 2-7M1A	
Nickname: DPAK+	

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